



PATENT ABSTRACTS OF JAPAN

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(54) VERTICAL RESONATOR TYPE
SEMICONDUCTOR LIGHT EMITTING ELEMENT
AND VERTICAL RESONATOR TYPE
SEMICONDUCTOR LIGHT EMITTING DEVICE

(57) Abstract:

PROBLEM TO BE SOLVED: To obtain an element which has no characteristic deterioration due to moisture absorption and high reliability as a vertical resonator type semiconductor element which uses AlGaAs of high Al composition for a substrate- surface side DBR mirror.

SOLUTION: On the substrate-surface side DBR mirror, a semiconductor layer including an InGaP layer functioning as a dampproof layer is provided to stop the AlGaAs-based DBR mirror of high Al composition from deteriorating in characteristics owing to moisture absorption.

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